

# QSE243

## Low Light Rejection Plastic Silicon Infrared PhotoTransistor

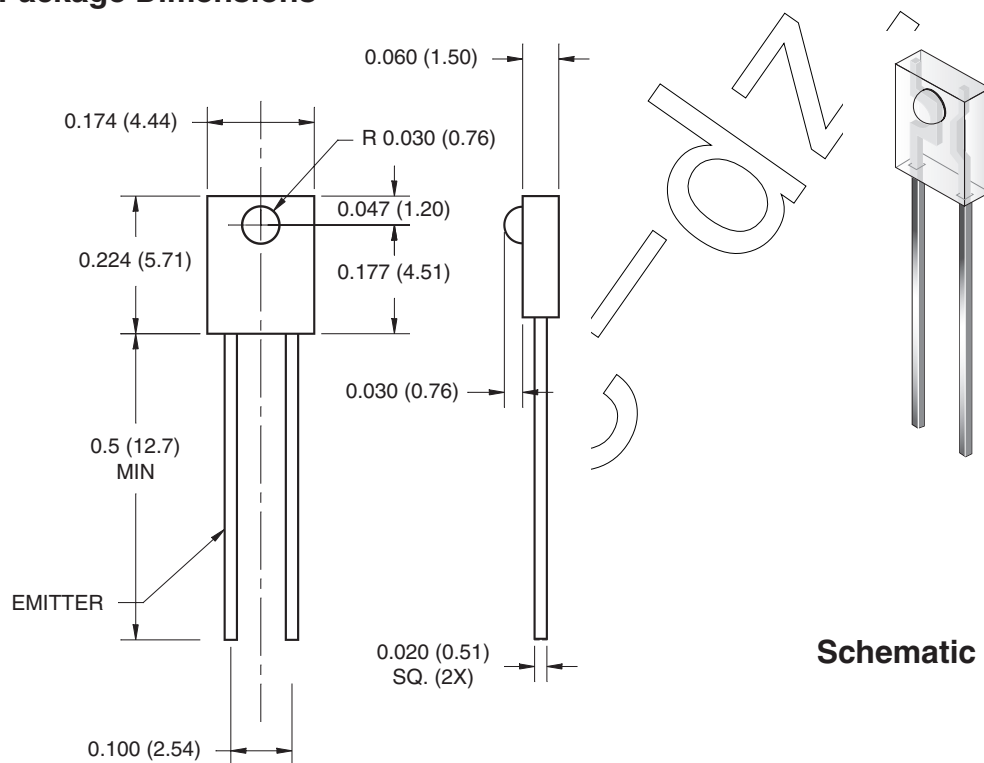
### Features

- NPN Silicon Phototransistor with internal base-emitter resistance
- Package Type: Sidelooker
- Medium Reception Angle, 50°
- Clear Plastic Package
- Matching Emitter: QEE213

### Description

The QSE243 is a silicon phototransistor with low light level rejection, encapsulated in a medium angle, thin clear plastic sidelooker package.

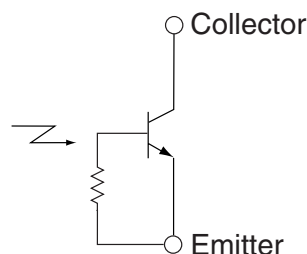
### Package Dimensions



#### NOTES:

1. Dimensions for all drawings are in inches (mm).
2. Tolerance of  $\pm 0.010$  (.25) on all non-nominal dimensions unless otherwise specified.

### Schematic



**Absolute Maximum Ratings** ( $T_A = 25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Rating	Unit
Operating Temperature	$T_{OPR}$	-40 to +100	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-40 to +100	$^\circ\text{C}$
Soldering Temperature (Iron) <sup>(2,3,4)</sup>	$T_{SOL-I}$	240 for 5 sec	$^\circ\text{C}$
Soldering Temperature (Flow) <sup>(2,3)</sup>	$T_{SOL-F}$	260 for 10 sec	$^\circ\text{C}$
Collector-Emitter Voltage	$V_{CE}$	30	V
Emitter-Collector Voltage	$V_{EC}$	5	V
Power Dissipation <sup>(1)</sup>	$P_D$	100	mW

**Electrical/Optical Characteristics** ( $T_A = 25^\circ\text{C}$  unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Units
Peak Sensitivity		$\lambda_{PS}$	—	880	—	nm
Reception Angle		Q	—	$\pm 25$	—	Deg.
Collector Emitter Dark Current	$V_{CE} = 15\text{ V}, E_e = 0$	$I_D$	—	100	—	nA
Collector Emitter Breakdown	$I_C = 100\text{ }\mu\text{A}$	$BV_{CEO}$	30	—	—	V
Saturation Voltage	$E_e = 1\text{ mW/cm}^2, I_C = 0.1\text{ mA}^{(5)}$	$V_{CE(SAT)}$	—	—	0.4	V
Rise Time	$V_{CC} = 5\text{ V}, R_L = 1000\text{ }\Omega$	$t_r$	—	15	—	$\mu\text{s}$
Fall Time	$I_C = 1\text{ mA}$	$t_f$	—	15	—	$\mu\text{s}$
Light Current Slope <sup>(6)</sup>	$V_{CE} = 5\text{ V}, E_{e1} = 1\text{ mW/cm}^2^{(5)}$ $E_{e2} = 0.5\text{ mW/cm}^2^{(5)}$	$I_{LS}$	1.0	—	—	$\text{mA/mW/cm}^2$
Knee Point <sup>(5,7)</sup>	$V_{CE} = 5\text{ V}$	$E_{ek}$	—	0.125	—	$\text{mW/cm}^2$

**Notes:**

- Derate power dissipation linearly 1.33 mW/ $^\circ\text{C}$  above  $25^\circ\text{C}$ .
- RMA flux is recommended.
- Methanol or isopropyl alcohols are recommended as cleaning agents.
- Soldering iron 1/16" (1.6 mm) minimum from housing.
- $\lambda = 950\text{ nm}$  GaAs.
- The slope is defined by  $(I_{C1} - I_{C2}) / (E_{e1} - E_{e2})$  where  $I_{C1}$  is the collector current at  $E_{e1}$  and  $I_{C2}$  the collector current at  $E_{e2}$ .
- Knee point is defined as being required to increase  $I_C$  to  $50\text{ }\mu\text{A}$ .

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